

Supporting Information

0D-3D Mixed-Dimensionality Perovskite $\text{Cs}_4\text{Pb}(\text{BrCl})_6\text{-CsPbBr}_{2-x}\text{Cl}_{1+x}$ Films for Stable and Sensitive Self-Powered, High-Temperature Photodetectors

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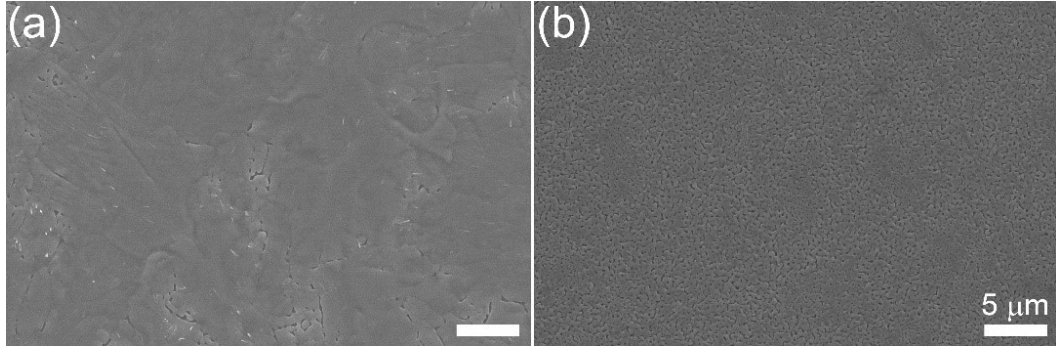


Fig. S1. SEM images of (a) PbBr_2 films and (b) PbBr_2 films prepared with 0.10 M CsCl additive.

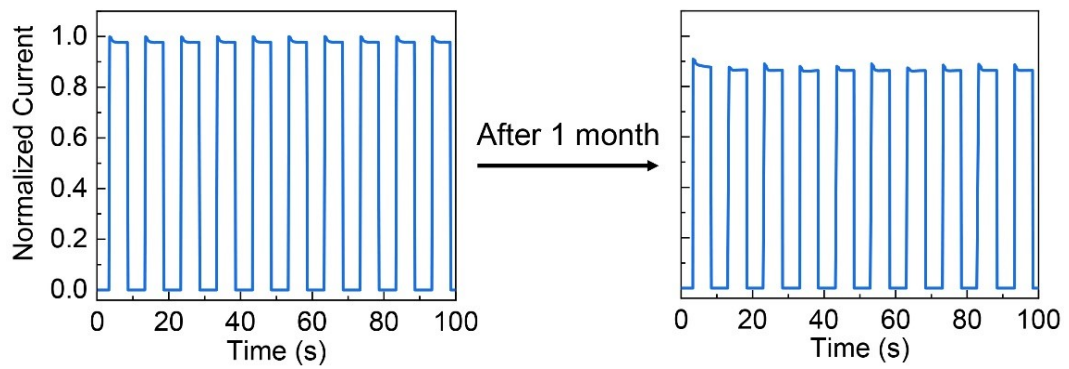


Fig. S2. Storage stability test results in ambient air for the self-powered PD based on $\text{CsPb}(\text{BrCl})_6\text{-CsPbBr}_{2-x}\text{Cl}_{1+x}$ film recorded under 300 °C.

Table S1. Summary of performance parameters of the typical PDs based on CsPbX₃ materials.

PD configuration	Self-powered	R (A W ⁻¹)	D* (Jones)	Rising/falling time	Ref.
FTO/TiO ₂ /Cs ₄ Pb(BrCl) ₆ -CsPbBr _{2-x} Cl _{1+x} /Carbon	Yes	0.18	1.65×10 ¹³	1.23 μs	This work
Au/CsPbBr ₃ /Au	No	133@5V	0.86 × 10 ¹² @5V	20.9/24.6 ms	[1]
CsPbBr ₃ /PDVT-10/Cr/Cu	No	1.64×10 ⁴ @3V	3.17×10 ¹² @3V	-	[2]
ITO/CsPbBr ₃ /ITO	No	6×10 ⁴ @3V	-	0.5/1.6 ms	[3]
Carbon/(HDA)CsPb ₂ Br ₇ /Carbon	No	0.21×10 ⁻³ @10V	1.5×10 ⁹	200/300 μs	[4]
ITO/PTAA/FAPbI ₃ /C ₆₀ /BCP/Cu	Yes	0.45	1.18×10 ¹²	0.9/1.3 μs	[5]
ITO/PTAA/PMMA/Cs _x DMA _{1-x} PbI ₃ /PCBM/Bphen/Cu	Yes	0.38	1×10 ¹³	558 ns	[6]
Au/(FAPbI ₃) _{0.79} (MAPbBr ₃) _{0.13} (CsPbI ₃) _{0.08} /Au	No	40@3 V	1.9×10 ¹³ @3 V	-	[7]
FTO/TiO ₂ /Al ₂ O ₃ /PCBM/MAPbI ₃ /Spiro-OMeTAD/Au/Ag	No	0.4@-1 V	6×10 ¹² @-1 V	1.2/3.2μs	[8]
ITO/MAPbI ₃ /Au	No	-	1.76×10 ¹¹ @2V	27.2/26.2 ms	[9]
Ag/ITO/Cs ₂ SnI ₆ /ITO/Ag	No	130@-5V	1×10 ¹³ @-5V	1/1 s	[10]
Au/Cs ₂ SnCl _{6-x} Br _x /Au	No	-	2.71×10 ¹⁰ @-20V	9.52/4.34 ms	[11]
Ag/Cs ₃ Bi ₂ I ₉ /Au	No	-	3.90×10 ¹¹ @3V	1.5/42.2 μs	[12]

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